L Number		Search Text	DB	Time stamp
		356/\$.ccls. and (gate adj oxide)	USFAT;	2003/07/02 14:04
			US-PGFUE; EFO; JPO;	
			DEFWENT; IEM TIB	
_	5.9	356 \$.ccls. and (gate adj oxide)	USEAT	0003/07/02 14:05
-	5	(gate adj oxide) and thickness and (high\$1k) and scatter\$	USPAT	2003 07:02 15:19
-		1356-\$.cols. and (gate adj oxide) and thickness	USEAT; US-PGEUB;	2003/07/02 15:05
			EPO; CPO; DEPWENT; IBM_TDB	
-	231	halliyal-arvind singh-bhanwar supramanian-ramkumar).in.	USPAT; US-PGPUB; EPO; JPO;	2003/07/02 15:26
			DEFWENT; IBM TDB	. (3)
-	18	subramanian-ramkumar).in. and (gate adj	USFAT; US-PGPUB;	0003 07:00 15:06
		oxide) and thickness	DESWENT; IBM TOB	
-	22	356/\$.cols. and (gate adj oxide) and (thickness or uniform\$) and scatter\$	USFĀT	2003/07/08 14:44
-	28	356/\$.cols. and (gate adj cxide) and (throkness or uniform\$) and scatter\$	USPAT; US-PGPUB; EPO; JPO;	0003/07/05 16:56
			DEFWENT; IBM_TDB	
-	9	:"4710030"   "4750822"   "5296970"     "5818526"   "5798837"   "5978074"     "6060374"   "6081330"   "6381009").PN.	USFĀT	2003/07/03 16:18
-	5	"4710030"   "4750822"   "5298970"   "5603526"   "5798837"   "5976074"	USPAT	2003/07/09 16:29
_	0	"60603"4"   "6081330"   "6351009").PN. and scatter\$   ("4710030"   "4750822"   "5298970"	USFAT	2003 07/08 16:29
		"5603526"   "579883'"   "5978074"   "6060374"   "6081330"   "6391009").PN. and		
-	32	scatter\$ and (gate adj oxide) 050/\$.cols. and (gate adj oxide) and othrokness or uniform\$) and scatter\$	USEAT	2003/07/08 16:30
-	30	250'\$.cols. and (gate adj oxide) and (thickness or uniform\$) and scatter\$ not	USFAT	2003/07/08 16:30
-	33	356/\$.ccls. 256/\$.ccls. and (gate adj oxide) and (thickness or uniform\$) and scatter\$ not	USFAT; US-PGFUB;	2003:07/08 16:45
		356 \$.ccls.	EFO; JPI; DEFWENT;	
-		   ((gate adj oxide) with (thickness or   uniform\$))   and scatter\$	IBM_TDB USPAT; US-PGFUE;	2003 07 09 12:10
:			DEFWENT; IBM TOB	
-	19	((gate adj exide) with (thickness or uniform\$)) and scatter\$.clm.	USSAT; US-PGPUB; EFC; JPD;	2003 07 03 16:46
			DEFWENT; IBM_TDB	
-	2	356/63)-632.ccls. and (gate adj oxide) and scatters	USPAT; US-PGPUB; EEO; JPO;	12003/07/09 16:26 -
t- (. 4 -			DERWENT; JEM_TDB	
-	14	((gate adj oxide) with (thickness or uniform\$)).ab. and scatter\$	USPĀT; US-PGPUB; EPO; JPO;	2003/07/09 12:38
\$ ·			DERWENT; IBM_TDB	

,	<del>-</del> -			
-	)	("5862054" "6060374" "5880040").pn. and	USPAT	2003/07/09 13:37
4	1	scatter\$		
-		("5862054" "6160374" "5881040").pn.	JSPAT	2003/07/09 15:11
_	9452		USPAT;	2003/17/09 13:41
İ	1	257 eJl.193,eL9.162 700/121,108,109	US-PGPUB;	
		[TELF181].ccls. ((gate adj oxide) with	EPO; JPO;	
1		thickness or uniform\$10 and scatter\$ and	DEFWENT;	
1		nitrid\$ or nitrogen\$)	IBM TEB	
	9035	4387163,786,614,14-18,769	USFĀT;	12013:17/09 12:41
1	•	257-a11.193,e19.161 700/121,108,109	US-PGFUE;	
		[7(2/131).ccls. ((gate adj oxide) with	EPO; JPO;	
į		thickness or uniform\$!! and scatter\$.ab.	CERWENT;	1
i i	İ	and mitrids or mitrogens.	IBM TUB	
1	4		USPAT:	2003/07/09 12:44
_	, ,	257/e21.193,e29.161 700/121,108,109	US-PGFUB;	LUCCIC /: JP 12:44
-				1
		702/101).cols. and ((gate adj oxide) with	EPG; JPG;	i
		thickness or uniform\$11 and scatter\$.ab.	CEFWENT;	
		and :nitrid\$ ir nitrogen\$.	IBM_TIB	
-	1	(435/263,786,814,14-18,769	∵SFĀT;	1003/07/09 11:45
		251 e21.193,e29.162 700/121,108,109	TS-PGFUE;	
		702/181).cols. and ((gate adj oxide) with	EPO; JPO;	
		thickness or uniform\$11.ab. and scatter\$	DEFWENT;	
1		and hitrid\$ ir hitrogen\$'	IBM TEB	
_	3:		USFAT;	2003/07/10 15:43
		257/e21.193,eL9.162 700/121,108,109	US-PGFUE;	
		702/181).cols. and ((gate adj oxide) with	EPO; JPO;	
		thickness or uniformall and scatters and	DEFWENT;	
	_	:nitrid\$ or nitrogen\$)	IBM_TDB	1
-	1	:"6508433" "5904523" "6060374").pn.	ISPAT	2003/07/09 15:12
_	1 2	"20020023900" "20030042432").pn.	US-PGPUE	2003/07/09 15:13
-	116		USFAT;	1003,07 39 16:26
	!	wafer) and scatter\$	US-PGPUB;	
1	i		EPO; JPO;	
	1		CERWENT;	
			IBM FDB	
_	10	356 630-632.cols. and (semiconductor or	"SFĀT;	2003/07/10 11:43
		wafer) and scatter\$.ab.	TS-PGFUE;	
		, war in and blacestrian.	EPO; CPO;	
			SEFWENT;	
		• •	IBM TUB	
+	,	356,630-632.ccls. and (semiconductor or	USFAT;	2003/07 09 16:36
_			US-PGPUB:	2003,07 09 10.39
1		wafer) and (scatterometry with thickness)		
1	1		EPO; JPO;	
1			DEFWENT;	
İ			IBM_TDB	
-		(scatterometry with nitrogen) and	USFAT;	1003/07/09 16:36
		(semiconductor or wafer)	US-PGFUE;	
1			EPO; JPO;	
_4	i		DEPWENT;	
	:		IBM TEB	
_	(	.scatterometry with nitrogen)	USEĀT;	2003/07:09 16:36
	1		TS-PGFUB;	
	!		EP1; CP0;	
	ı		DEFWENT;	
	1			
			IBM_TLB	2003/07/09 16:36
-	6/9	scatter\$ with nitrogen)	USFĀT;	5003/Cluba 10:30
4			US-PGFUB;	
			EPO; JPO;	
,	I.		DEFWENT;	
1	1	1	IBM_TDB	
-	195	scatter\$ with nitrogen) and	USFĀT;	2003,07,09 16:37
1	1	semiconductor or wafer or (gate adj	US-PGPUE;	
		oxide!)	EPI; JPI;	
· -	1		DEFWENT;	
			: IBM TUB	
	55	scarter\$ with nitrogen) and	USFĀT;	2003/07/09 16:39
	J D	swaller with hitrogen, and Semisonductor or wafer or date adj	: US-PGPUB;	1
			. 05°PGPUE; ! EPD; JPD;	:
		, chide ( and Scatterp.aD.		
			DERWENT;	
			IBM_TDB	· · · · · · · · · · · · · · · · · ·

F'-	47	(scatter\$ with nitrogen) and	USPAT;	2013/07/09 15:40
		(semiconductor or wafer or (gate adj	US-PGPUB;	
		oxide) and scatter\$.ab. not (electron	EPI; JPD;	
		near4 beam)	DEFWENT;	
	2 -		IBM_TCB   USFAT;	12003/07/09 16:40
_	20	scatter\$ with nitrogen) and semiconductor or wafer or gate adj	US-PGFUE;	1 1033 37 09 16:40
'		semilibriuseer or water or gate adj   bxide)   and (scatter\$ and (nitrogen or	EP1; JP0;	
		oxide/ and (scatters and (nitrogen or   nitridgs)).ab. not (electron near4 beam)	DEFWENT;	
		nittriums)).ab. not Refection near4 beam)	IBM TEB	
	5	   "5367076"   "5377860"   "5380833"	USFAT	2003/07 10 10:16
_	7	356776	CSFAI	2003/07 10 11:10
		6351546		1
	1	6243354   6353666   6423 <i>577 7.</i> EN.  -"5867276"   "5877880"   "5893838"	USFAT	2003/07-10 11:18
	1	"6051348"   "6081334"   "6141107"	CCFAI	2005 37.15 11.10
		0001346		
		scatter\$.ab.		
_	.1		USFAT	2003/07/10 11:17
	4	"5703692").PN.	CCFAI	2000.07710 11.17
	4	3.03692	USFAT	2003/07/10 11:18
	4	"6051348"   "6081334"   "6141107"	COLMI	2.25.27742 12.10
		66,31346		
		bladiea   bdddood   baller// ).rn. and     scatteromet\$		
_	17	35%/631-631.cols. and (sem conductor or	   USFAT;	2003/07/10 12:01
	1	wafer)   and scatterem\$	US-PGFUB:	2133737710 12.01
		- wis 51, and Scacceromy	EPO; JPO;	
			DESWELT:	
			IBM TEB	
	16	356/630-630.ccls. and (semiconductor or	USPAT:	2003/07/10 11:43
	10	wafer) and scatterom\$ not scatter\$.ab.	US-PGFUE;	2300707711 11.45
		ware;) and Statteremp ner Statter, ab.	EPO; JPO;	
			DEFWENT;	
			IBM TDB	
l _	ñ	356 237.4,237.5.ccls. and (semiconductor	USFĀT;	2003/07/10 14:17
	J	or wafer) and scatterom\$ and thickness	US-PGFUB;	2
		dia dedecata managementa di an	EPG; JPG;	
			DEFWENT;	
			IBM TDB	
_	7	250/559.27.cols. and (semiconductor or	USEĀT;	2003, 07 10 11:55
		wafer) and scatterem\$	US-PGFUB;	
			EPO; JPO;	
			DEFWENT;	
			IBM TDB	
-	1	250 559.27.cols. and (semiconductor or	USPĀT;	2003/07/10 11:55
		waier) and scatterom\$	EPO; JPO;	
			DEFWENT;	
			IBM TUB	
-	21	35% 631-632.cols. and scatterom\$	USPĀT;	12103 07 13 12:01
			US-PGPUE;	
			EPC; JPC;	
			DEFWENT;	
1			IBM_TDB	
-	10	35r 6363L.cols. and scatterom\$	USEĀT	12:13 67 13 12:01
-		35r 63 -631.cols. and scatter\$	USFAT	(2003 07 10 12:01
_		35% 63632.cols. and scatter\$.ab.	USFAT	12003.07 10 12:02
-	20	35% 63)-632.cols. and scatter\$.ab. and	USFAT	2003-07 10 12:02
		scatterS	1	
_	3.5	356 \$.ccls. and (semiconductor or wafer)	USPAT;	2003/07/10 14:17
		and scatterom\$.ab.	US-PGFUB;	
			EPO; JPO;	
			DEFWENT;	
			IBM_TDB	i
-		("3393624"   "5867276"   "5923423"	¦ USPĀT	2003/07/10 15:27
		"6100995"   "6259521"   "6266125"	:	
		"6)-6253"   "6424417"].PN.	!	1
_	2	: {"1393624"   "5867276"   "5923423"	USPAT	· 2003/07/10 15:27
;		"6100985"   "b259521"   "6266125"	1	
		"6186253" · "6424417").PN. and (nitrogens		
		or nitride\$'		
	-			

-	61	(438/263,736,514,14-18,769	USPAT;	2003/07/10	15:54
		257/e21.193,e29.162 700/121,108,109	US-PGPUB;		
İ		702/181).ccls. and ((gate adj oxide) with	EPO; JPO;		
		evd)	DEFWENT;		
			IBM TDB		
-	19	(438/263,786,514,14-18,769	USFAT;	2003/07/10	15:57
		257/e21.193,e29.162 700/121,108,109	US-PGPUB;		
		702/181).ccls. and (gate adj oxide).ab.	EPO; JPO;		
		and ((gate adj oxide) with cvd)	DERWENT;		
		- · · · · · · · · · · · · · · · · · · ·	IBM TDB		